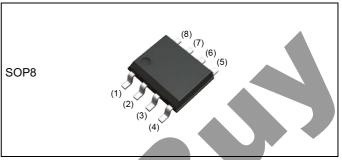
30V Nch / Nch+SBD Power MOSFET

Cymbol	Tr1	Tr2
Symbol	Nch	Nch+SBD
V_{DSS}	30V	30V
R _{DS(on)} (Max.)	24.0mΩ	19.6mΩ
I _D	±7.0A	±8.5A
P_D	2.0)W

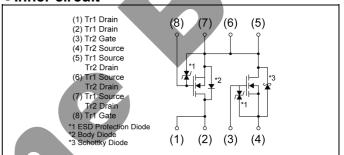
Features

- 1) Low on resistance
- 2) Small Surface Mount Package (SOP8)
- 3) Pb-free lead plating; RoHS compliant
- 4) Halogen Free

Outline



Inner circuit



Packaging specifications

or achai	ing specifications	
	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	12
	Quantity (pcs)	2500
	Taping code	TB
	Marking	SH8K10S

Application

Switching

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

		• ,			
Parame	tor	Symbol	Tr1	Tr2	Unit
and the tel		Symbol	Nch	Nch+SBD	Offic
Drain - Source voltage		V_{DSS}	30	30	V
Continuous drain current		I _D	±7.0	±8.5	Α
Pulsed drain current		I _{DP} *1	±28	±34	Α
Gate - Source voltage		V_{GSS}	±20	±20	V
Day or dissination	total	P _D *2	2.0		۱۸/
Power dissipation	Power dissipation total		1	.4	W
Junction temperature		T _j	1	50	°C
Operating junction and storage	e temperature range	T _{stg}	-55 to	+150	°C

●Thermal resistance

Parameter		Cymah al		Values		Llmit
Parameter		Symbol	Min.	Тур.	Max.	Unit
Thermal registance innetion, embient	total	R _{thJA} *2	-	-	62.5	°C/W
Thermal resistance, junction - ambient	total	R _{thJA} *3	-	-	89.2	C/VV

● Electrical characteristics (T_a = 25°C)

Davarantan	Curanh a l	T	Canditions		Values		l limit
Parameter	Symbol	Type	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown	V	Tr1	$V_{GS} = 0V, I_D = 1mA$	30	-		V
voltage	V _{(BR)DSS}	Tr2	$V_{GS} = 0V, I_D = 1mA$	30	-		V
Breakdown voltage	ΔV _{(BR)DS} S	Tr1	I _D = 1mA, referenced to 25°C	-	29	-	mV/°C
temperature coefficient	ΔT _j	Tr2	I _D = 1mA, referenced to 25°C	-	29	-	IIIV/ C
Zero gate voltage	I _{DSS}	Tr1	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
drain current	IDSS	Tr2	$V_{DS} = 30V, V_{GS} = 0V$) -	-	500	μΛ
Gate - Source	I _{GSS}	Tr1	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±10	μΑ
leakage current	'GSS	Tr2	$V_{DS} = 0V$, $V_{GS} = \pm 20V$	-	-	±10	μ, τ
Gate threshold	$V_{GS(th)}$	Tr1	$V_{DS} = 10V, I_{D} = 1mA$	1.0	-	2.5	V
voltage	V GS(th)	Tr2	V_{DS} = 10V, I_D = 1mA	1.0	-	2.5	V
Gate threshold voltage	$\Delta V_{GS(th)}$	Tr1	I _D = 1mA, referenced to 25°C	-	-1.6	-	mV/°C
temperature coefficient	ΔT_{j}	Tr2	I _D = 1mA, referenced to 25°C	-	-1.6	-	11117 0
			$V_{GS} = 10V, I_D = 7.0A$	-	17.0	24.0	
		Tr1	$V_{GS} = 4.5V, I_D = 7.0A$	-	23.0	33.0	
Static drain - source	R _{DS(on)} *4		$V_{GS} = 4.0V, I_D = 7.0A$	-	25.0	35.0	mΩ
on - state resistance	TUS(on)		$V_{GS} = 10V, I_D = 8.5A$	-	14.0	19.6	11122
		Tr2	$V_{GS} = 4.5V, I_D = 8.5A$	-	17.8	24.9	
			$V_{GS} = 4.0V, I_D = 8.5A$	-	19.0	26.6	
Forward Transfer	Y _{fs} *4	Tr1	$V_{DS} = 10V, I_{D} = 7.0A$	5.0	-	-	S
Admittance	l 'tsi	Tr2	$V_{DS} = 10V, I_{D} = 8.5A$	8.0	-	-	

^{*1} Pw ≦ 10µs, Duty cycle ≦ 1%

^{*2} Mounted on a ceramic board (30×30×0.8mm)

^{*3} Mounted on a Cu board (25×25×0.8mm)

^{*4} Pulsed

●Electrical characteristics (T_a = 25°C)

<Tr1>

Parameter	Symbol Conditions -		,	Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	V _{GS} = 0V	1	660	1	
Output capacitance	C _{oss}	V _{DS} = 10V	-	200	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	120	-	
Turn - on delay time	t _{d(on)} *4	$V_{DD} \simeq 15V$, $V_{GS} = 10V$	-	8		
Rise time	t _r *4	I _D = 3.5A	-	10	-	D
Turn - off delay time	t _{d(off)} *4	$R_L = 4.29\Omega$	-	37		ns
Fall time	t _f *4	$R_G = 10\Omega$	-	11		

<Tr2>

Input capacitance C_{iss} $V_{GS} = 0V$ Output capacitance C_{oss} $V_{DS} = 10V$ Reverse transfer capacitance C_{rss} $f = 1MHz$ Turn - on delay time $t_{d(on)}^{*4}$ $V_{DD} = 15V$,	Conditions	Y 3	Values		Linit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C _{iss}	V _{GS} = 0V	-	830	-	
Output capacitance	C _{oss}	V _{DS} = 10V	1	250	1	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	ı	95	ı	
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} \simeq 15V$, $V_{GS} = 10V$	ı	11	ı	
Rise time	t _r *4	I _D = 4.0A	-	27	-	ne
Turn - off delay time	t _{d(off)} *4	$R_L = 3.75\Omega$	ı	49	ı	ns
Fall time	t _f *4	$R_G = 10\Omega$	ı	15	ı	



● Gate charge characteristics (T_a = 25°C)

<Tr1>

Doromotor	Cumbal	Conditions	,	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q _g *4		-	8.4	16.8	
Gate - Source charge	Q _{gs} *4	V _{DD} ≈ 15V, I _D = 7.0A V _{GS} = 5V	-	1.9	-	nC
Gate - Drain charge	Q _{gd} *4	*GS	-	3.3	-	

<Tr2>

Parameter Total gate charge Gate - Source charge	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Offic
Total gate charge	Q _g *4		-	8.9	17.8	
Gate - Source charge	Q _{gs} *4	$V_{DD} \approx 15V, I_{D} = 8.5A$ $V_{GS} = 5V$		2.5	-	nC
Gate - Drain charge	Q _{gd} *4	7.63	6 -	2.6	-	

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

<Tr1>

Daramatar	Cymabal	Conditions	,	Values		Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	Is	T = 25°C	-	-	1.6	^
Pulse forward current	I _{SP} *1	T _a = 25°C	-	-	28	А
Forward voltage	V _{SD} *4	V _{GS} = 0V, I _S = 1.6A	-	-	1.2	V

<Tr2>

Doromotor	Symbol	Conditions	,	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I _S	T = 25°C	-	-	3.5	^
Pulse forward current	I _{SP} *1	T _a = 25°C	-	-	34	A
Forward voltage	V _{SD} *4	V _{GS} = 0V, I _S = 2.0A	-	0.45	0.50	V

Fig.1 Power Dissipation Derating Curve

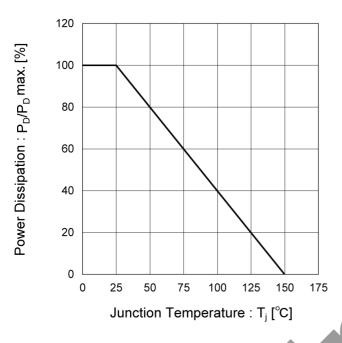
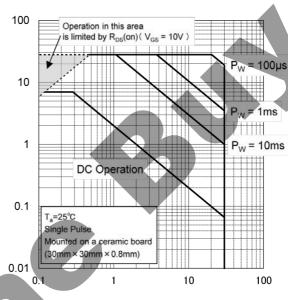


Fig.2 Maximum Safe Operating Area



Drain Current : I_D [A]

Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

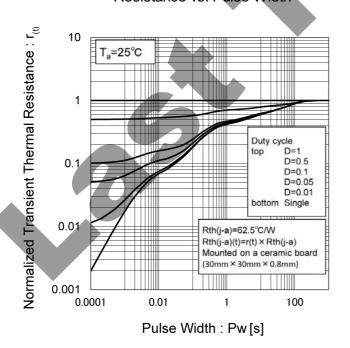
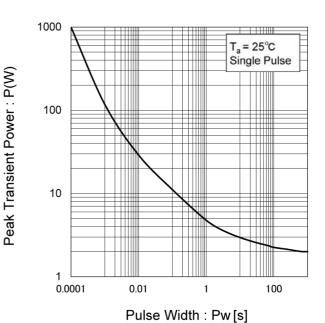


Fig.4 Single Pulse Maximum Power dissipation

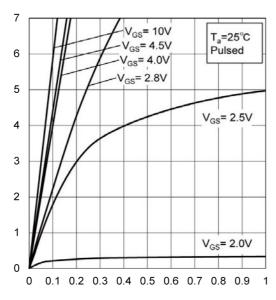


Drain Current : I_D [A]

Drain-Source Breakdown Voltage: V_{(BR)DSS} [V]

● Electrical characteristic curves < Tr1>

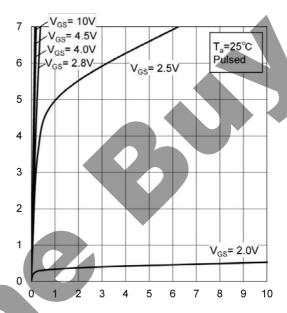
Fig.5 Typical Output Characteristics(I)



Drain Current : I_D [A]

Drain - Source Voltage : V_{DS} [V]

Fig.6 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

Fig.7 Breakdown Voltage vs.

Junction Temperature

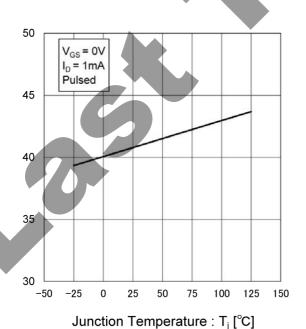


Fig.8 Typical Transfer Characteristics

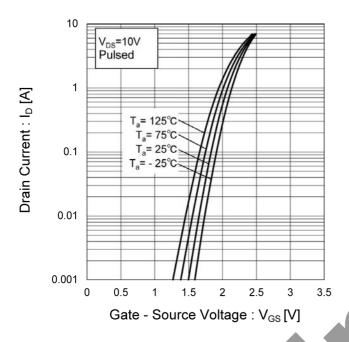


Fig.9 Gate Threshold Voltage vs.
Junction Temperature

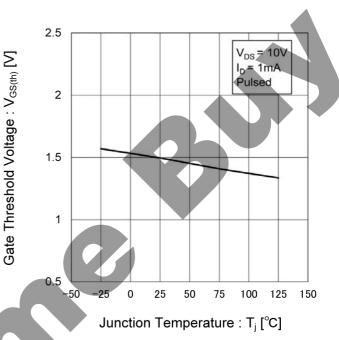
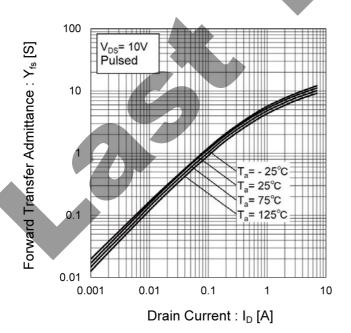


Fig.10 Forward Transfer Admittance vs.
Drain Current



7/18

Fig.11 Drain Current Derating Curve

120 100 Drain Current Dissipation 80 : I_D/I_Dmax. [%] 60 40 20 0 150 -25 0 25 50 75 100 125 Junction Temperature : T_j [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

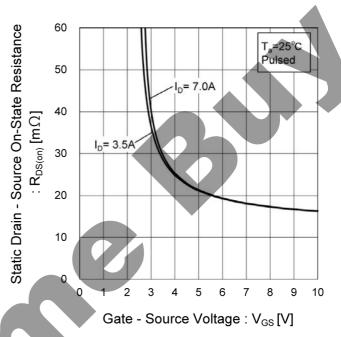
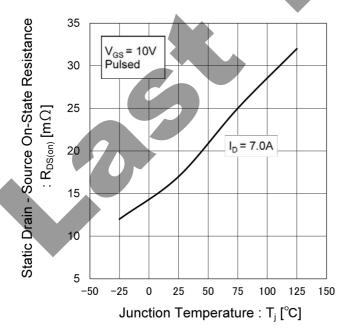


Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature



8/18

Fig.14 Static Drain - Source On - State
Resistance vs. Drain Current (I)

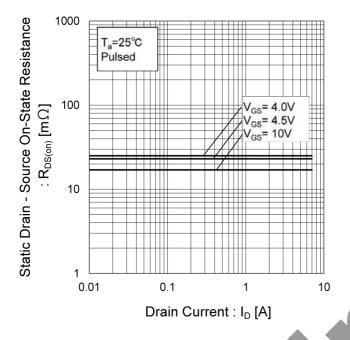


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

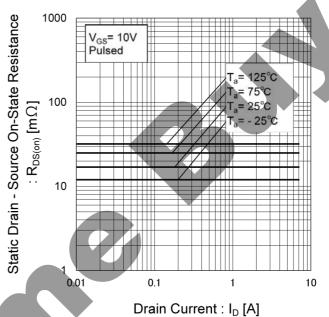


Fig.16 Static Drain - Source On - State
Resistance vs. Drain Current (III)

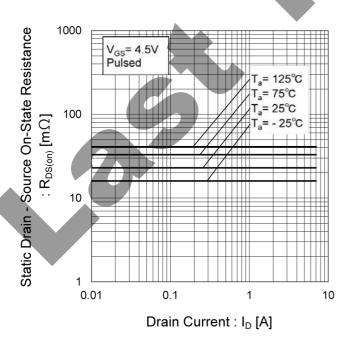


Fig.17 Static Drain - Source On - State
Resistance vs. Drain Current (IV)

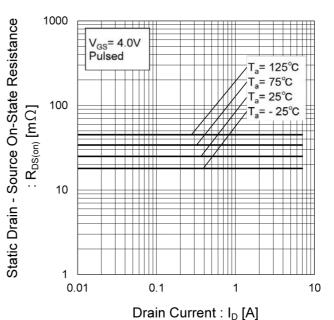


Fig.18 Typical Capacitance vs.

Drain - Source Voltage

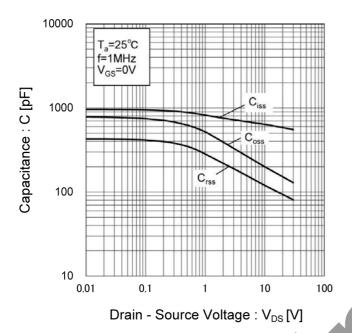


Fig.19 Switching Characteristics

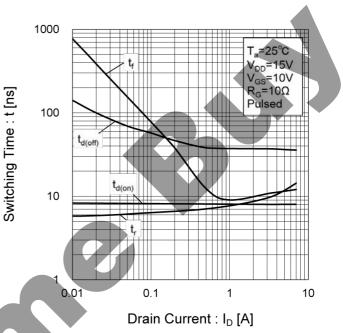


Fig.20 Dynamic Input Characteristics

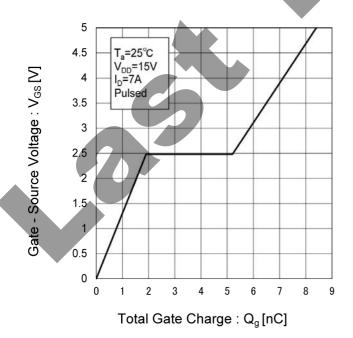


Fig.21 Source Current vs.

Source Drain Voltage

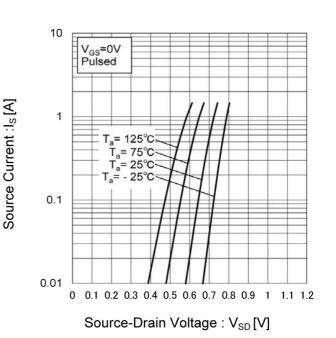


Fig.1 Power Dissipation Derating Curve

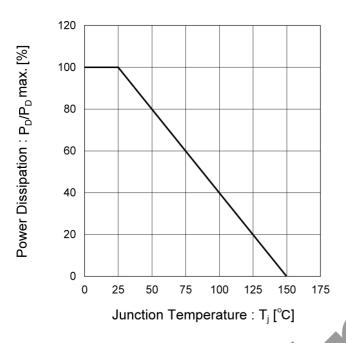
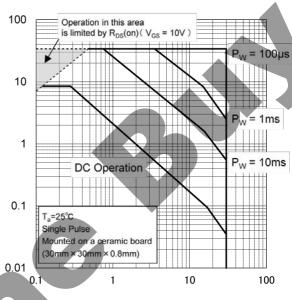


Fig.2 Maximum Safe Operating Area



Drain Current : I_D [A]

Drain - Source Voltage: V_{DS}[V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

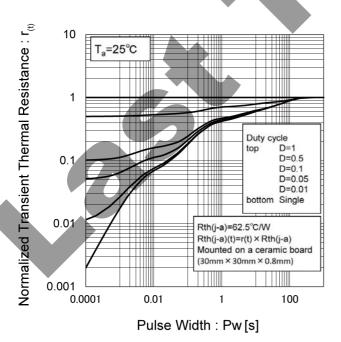
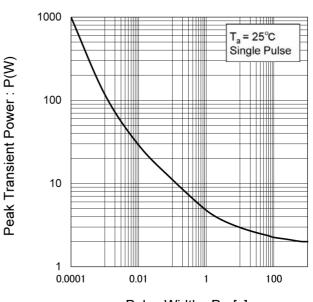
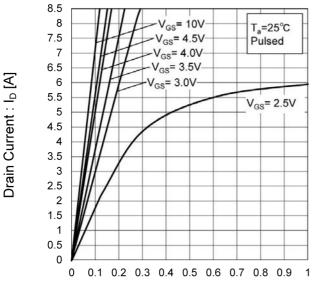


Fig.4 Single Pulse Maximum Power dissipation



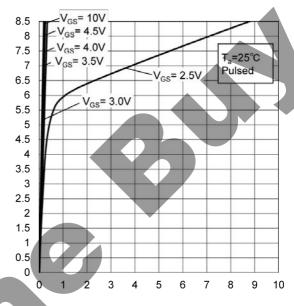
Pulse Width : Pw [s]

Fig.5 Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

Fig.6 Typical Output Characteristics(II)

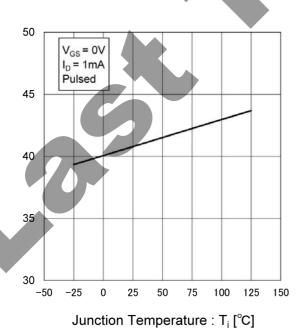


Drain Current : I_D [A]

Drain - Source Voltage : V_{DS} [V]

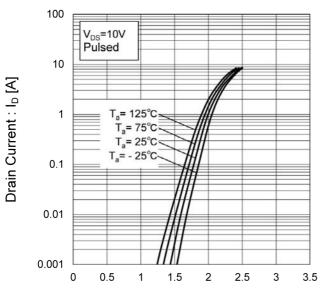
Fig.7 Breakdown Voltage vs.

Junction Temperature



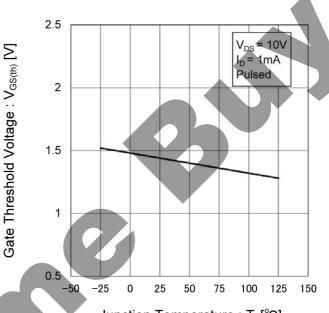
Drain-Source Breakdown Voltage: V_{(BR)DSS} [V]

Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : $V_{GS}[V]$

Fig.9 Gate Threshold Voltage vs.
Junction Temperature



Junction Temperature : T_j [°C]



Fig.10 Drain Current Derating Curve

120 100 Drain Current Dissipation 80 : I_D/I_Dmax. [%] 60 40 20 0 150 -25 0 25 50 75 100 125 Junction Temperature : T_j [°C]

Fig.11 Static Drain - Source On - State Resistance vs. Gate Source Voltage

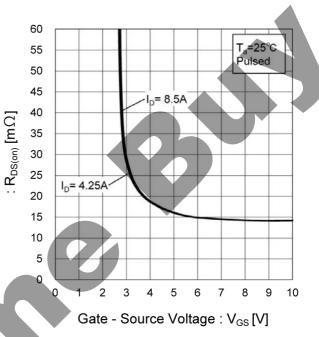
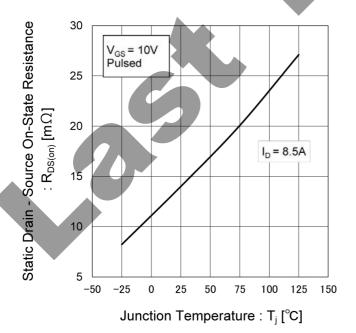


Fig.12 Static Drain - Source On - State
Resistance vs. Junction Temperature



Static Drain - Source On-State Resistance

Fig.13 Static Drain - Source On - State
Resistance vs. Drain Current (I)

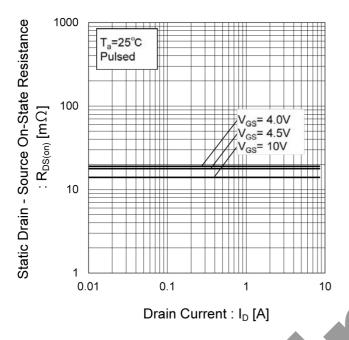


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (II)

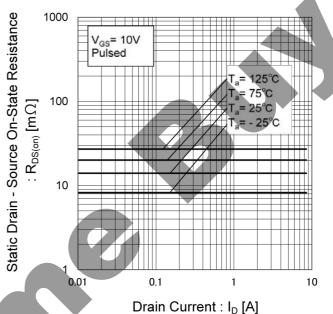


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (III)

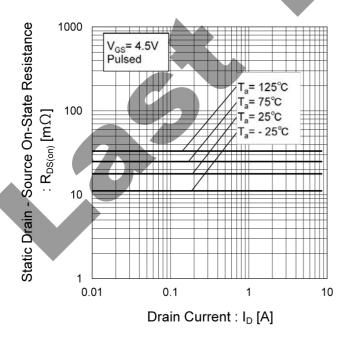


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (IV)

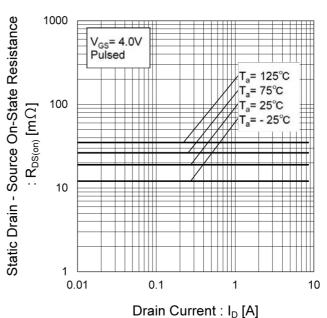


Fig.17 Typical Capacitance vs.

Drain - Source Voltage

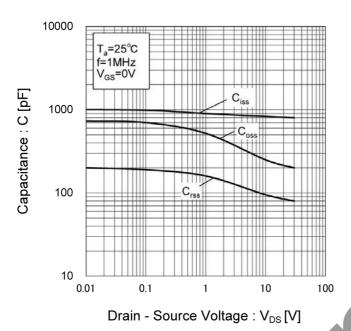


Fig.18 Switching Characteristics

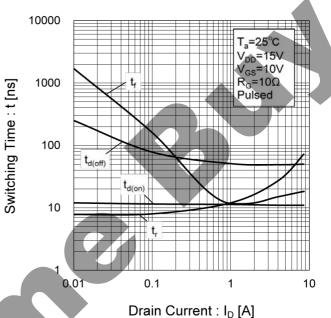


Fig.19 Dynamic Input Characteristics

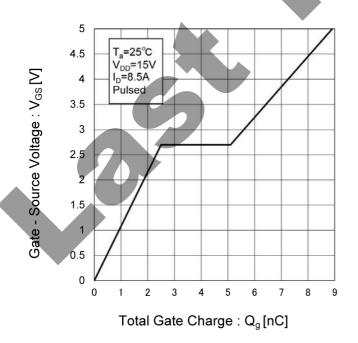
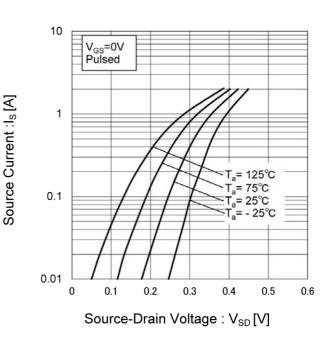


Fig.20 Source Current vs.

Source Drain Voltage



• Measurement circuits < It is the same for the Tr1 and Tr2>

Fig.1-1 Switching Time Measurement Circuit

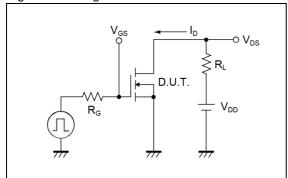


Fig.2-1 Gate Charge Measurement Circuit

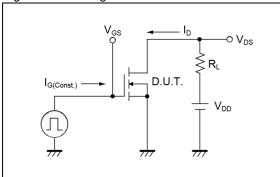


Fig.1-2 Switching Waveforms

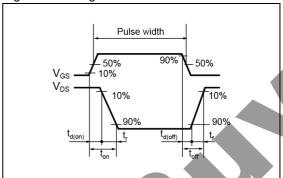
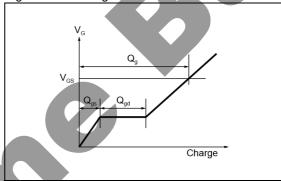


Fig.2-2 Gate Charge Waveform



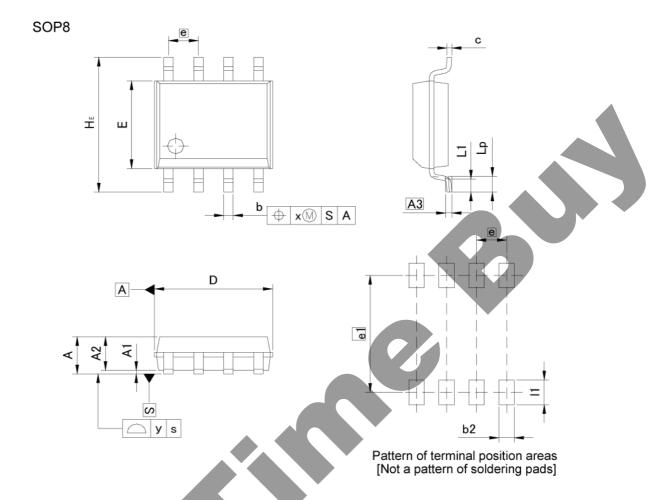
Notice

SBD has a large reverse leak current compared to other type of diode. Therefore; it would raise a junction temperature, and increase a reverse power loss. Further rise of inside temperature would cause a thermal runaway.

This built-in SBD has low VF characteristics and therefore, higher leak current. Please consider enough the surrounding temperature, generating heat of MOSFET and the reverse current.



Dimensions



DIM	MILIME	TERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	=	1.75	1	0.069
A1	0.1	5	0.0	06
A2	1.40	1.60	0.055	0.063
A3	0.2	5	0.0	10
b	0.30	0.50	0.012	0.020
С	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
е	1.2	7	0.0	50
HE	5.70	6.30	0.224	0.248
L1	0.40	0.60	0.016	0.024
Lp	0.65	0.85	0.026	0.033
x	0.1	5	0.0	06
У	0.1	0	0.0	04

DIM	MILIMETERS		INCHES	
DIM	MIN	MIN MAX MIN	MIN	MAX
b2	- 2	0.65	7 %	0.026
e1	5.15		0.203	
11	-0	1.15		0.045

Dimension in mm/inches



Notice

Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipment (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CL ACCTI
CLASSIV	CLASSIII	CLASSⅢ	CLASSIII

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

Precaution Regarding Intellectual Property Rights

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Notice-PGA-E Rev.004

General Precaution

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